Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(ild or interlayer near dielectric) and (integrated near circuit) and (alignment near mark41) and (hardmask or hard near mask) and (tan or tantalum near nitride) and (wavelength) and (resistiv$3) and (opening or aperture or hole or via) and (pattern$3 or etch43) and (conductiv43).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:27
L2	0	(ild or interlayer near dielectric) and (integrated near circuit) and (alignment near mark$1) and (hardmask or hard near mask) and (tan or tantalum near nitride) and (wavelength) and (resistiv$3) and (opening or aperture or hole or via) and (pattern$3 or etch43) and (conductiv43).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:28
L3	0	(ild or interlayer near dielectric) and (integrated near circuit) and (alignment near mark$1) and (hardmask or hard near mask) and (tan or tantalum near nitride) and (wavelength) and (resistiv$3) and (opening or aperture or hole or via) and (pattern$3 or etch43) and (conductiv43)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:28
L4	2	(ild or interlayer near dielectric) and (integrated near circuit) and (alignment near mark$1) and (hardmask or hard near mask) and (tan or tantalum near nitride) and (wavelength) and (resistiv$3) and (opening or aperture or hole or via) and (pattern$3 or etch43) and (conductiv$3).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:28
L5	2	(ild or interlayer near dielectric) and (integrated near circuit) and (alignment near mark$1) and (hardmask or hard near mask) and (tan or tantalum near nitride) and (wavelength) and (resistiv$3) and (opening or aperture or hole or via) and (pattern$3 or etch$3) and (conductiv$3).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:28

| L6 | 2 | (ild or interlayer near dielectric) and (integrated near circuit) and (alignment near mark$1) and (hardmask or hard near mask) and (tan or tantalum near nitride) and (wavelength) and (resistiv$3) and (opening or aperture or hole or via) and (pattern$3 or etch$3) and (conductiv$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/03 16:28 |